

AUIRF7379Q

HEXFET® Power MOSFET

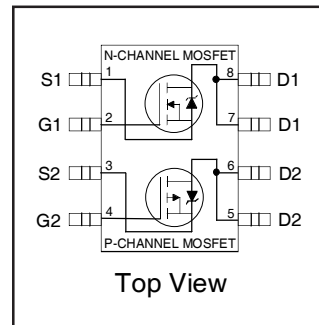
Features

- Advanced Planar Technology
- Low On-Resistance
- Dual N and P Channel MOSFET
- Surface Mount
- Available in Tape & Reel
- 150°C Operating Temperature
- Automotive [Q101] Qualified
- Lead-Free, RoHS Compliant

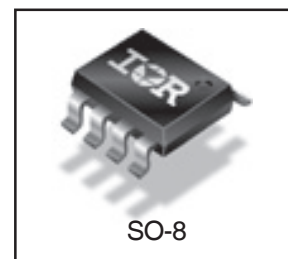
Description

Specifically designed for Automotive applications, these HEXFET® Power MOSFET's in a Dual SO-8 package utilize the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of these Automotive qualified HEXFET Power MOSFET's are a 150°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These benefits combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.

The efficient SO-8 package provides enhanced thermal characteristics and dual MOSFET die capability making it ideal in a variety of power applications. This dual, surface mount SO-8 can dramatically reduce board space and is also available in Tape & Reel.



	N-Ch	P-Ch
$V_{(BR)DSS}$	30V	-30V
$R_{DS(on)}$ typ.	0.038Ω	0.070Ω
	max. 0.045Ω	0.090Ω
I_D	5.8A	-4.3A



G	D	S
Gate	Drain	Source

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.		Units
		N-Channel	P-Channel	
V _{DS}	Drain-Source Voltage	30	-30	V
I _D @ T _A = 25°C	Continuous Drain Current, V _{GS} @ 10V	5.8	-4.3	A
I _D @ T _A = 70°C	Continuous Drain Current, V _{GS} @ 10V	4.6	-3.4	
I _{DM}	Pulsed Drain Current ①	46	-34	
P _D @T _A = 25°C	Power Dissipation	2.5		W
	Linear Derating Factor	0.02		
V _{GS}	Gate-to-Source Voltage	± 20		V
dv/dt	Peak Diode Recovery dv/dt ②	5.0	-5.0	V/ns
T _J T _{STG}	Operating Junction and Storage Temperature Range	-55 to + 150		°C

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient ④	—	50	°C/W

HEXFET® is a registered trademark of International Rectifier.

*Qualification standards can be found at <http://www.irf.com/>

Static Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise stated)

	Parameter		Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	N-Ch	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
		P-Ch	-30	—	—		$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	N-Ch	—	0.032	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1\text{mA}$
		P-Ch	—	-0.037	—		Reference to 25°C , $I_D = -1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	N-Ch	—	0.038	0.045	Ω	$V_{GS} = 10V, I_D = 5.8A$ ③
			—	0.055	0.075		$V_{GS} = 4.5V, I_D = 4.9A$ ③
		P-Ch	—	0.070	0.090		$V_{GS} = -10V, I_D = -4.3A$ ③
			—	0.130	0.180		$V_{GS} = -4.5V, I_D = -3.7A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	N-Ch	1.0	—	3.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
		P-Ch	-1.0	—	-3.0		$V_{DS} = V_{GS}, I_D = -250\mu A$
g_{fs}	Forward Transconductance	N-Ch	5.2	—	—	S	$V_{DS} = 15V, I_D = 2.4A$ ③
		P-Ch	2.5	—	—		$V_{DS} = -24V, I_D = -1.8A$ ③
I_{DSS}	Drain-to-Source Leakage Current	N-Ch	—	—	1.0	μA	$V_{DS} = 24V, V_{GS} = 0V$
		P-Ch	—	—	-1.0		$V_{DS} = -24V, V_{GS} = 0V$
		N-Ch	—	—	25		$V_{DS} = 24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
		P-Ch	—	—	-25		$V_{DS} = -24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage		—	—	± 100	nA	$V_{GS} = \pm 20V$

Dynamic Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise stated)

	Parameter		Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge	N-Ch	—	—	25	nC	N-Channel $I_D = 2.4A, V_{DS} = 24V, V_{GS} = 10V$
		P-Ch	—	—	25		
Q_{gs}	Gate-to-Source Charge	N-Ch	—	—	2.9		P-Channel ③ $I_D = -1.8A, V_{DS} = -24V, V_{GS} = -10V$
		P-Ch	—	—	2.9		
Q_{gd}	Gate-to-Drain ("Miller") Charge	N-Ch	—	—	7.9	ns	N-Channel $V_{DD} = 15V, I_D = 2.4A, R_G = 6.0\Omega$ $R_D = 6.2\Omega$
		P-Ch	—	—	9.0		
$t_{d(on)}$	Turn-On Delay Time	N-Ch	—	6.8	—		
		P-Ch	—	11	—		
t_r	Rise Time	N-Ch	—	21	—	ns	P-Channel ③ $V_{DD} = -15V, I_D = -1.8A, R_G = 6.0\Omega$ $R_D = 8.2\Omega$
		P-Ch	—	17	—		
$t_{d(off)}$	Turn-Off Delay Time	N-Ch	—	22	—		
		P-Ch	—	25	—		
t_f	Fall Time	N-Ch	—	7.7	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
		P-Ch	—	18	—		
L_D	Internal Drain Inductance	N-P	—	4.0	—		
L_S	Internal Source Inductance	N-P	—	6.0	—		
C_{iss}	Input Capacitance	N-Ch	—	520	—	pF	N-Channel $V_{GS} = 0V, V_{DS} = 25V, f = 1.0\text{MHz}$
		P-Ch	—	440	—		
C_{oss}	Output Capacitance	N-Ch	—	180	—		P-Channel $V_{GS} = 0V, V_{DS} = -25V, f = 1.0\text{MHz}$
		P-Ch	—	200	—		
C_{rss}	Reverse Transfer Capacitance	N-Ch	—	72	—		
		P-Ch	—	93	—		

Diode Characteristics

	Parameter		Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	N-Ch	—	—	3.1	A	
		P-Ch	—	—	-3.1		
I_{SM}	Pulsed Source Current (Body Diode) ①	N-Ch	—	—	46		
		P-Ch	—	—	-34		
V_{SD}	Diode Forward Voltage	N-Ch	—	—	1.0	V	$T_J = 25^\circ\text{C}, I_S = 1.8A, V_{GS} = 0V$ ③
		P-Ch	—	—	-1.0		$T_J = 25^\circ\text{C}, I_S = -1.8A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	N-Ch	—	47	71	ns	N-Channel $T_J = 25^\circ\text{C}, I_F = 2.4A, di/dt = 100A/\mu s$
		P-Ch	—	53	80		
Q_{rr}	Reverse Recovery Charge	N-Ch	—	56	84	nC	P-Channel ③ $T_J = 25^\circ\text{C}, I_F = -1.8A, di/dt = 100A/\mu s$
		P-Ch	—	66	99		

Notes ① through ④ are on page 10

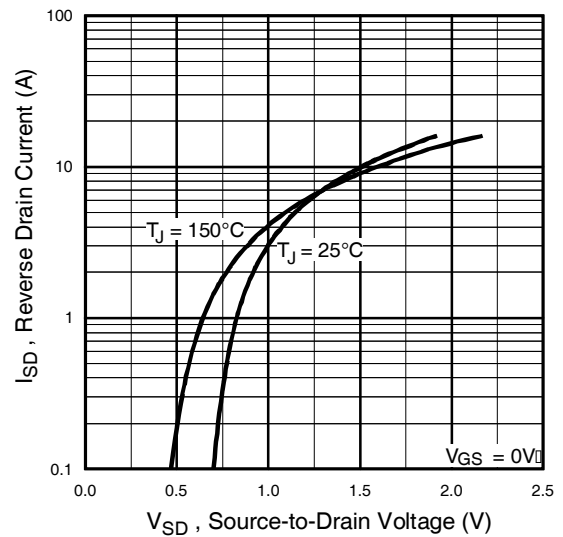
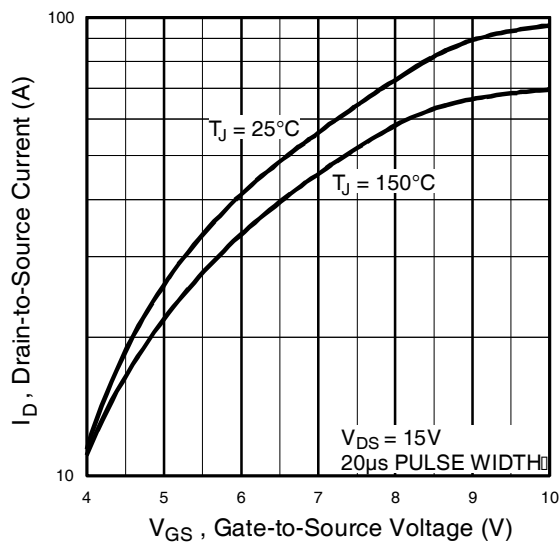
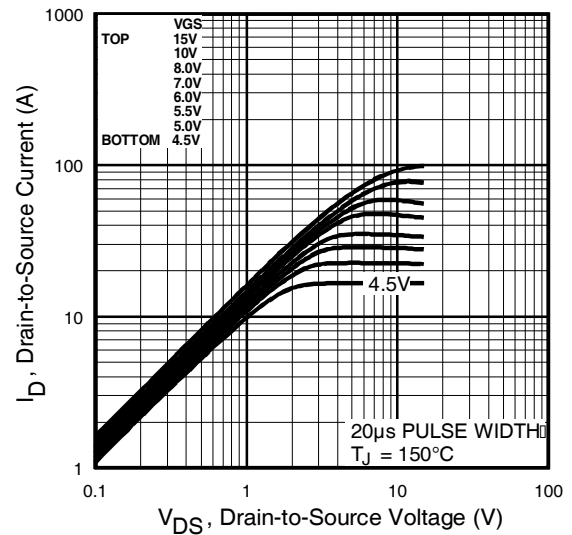
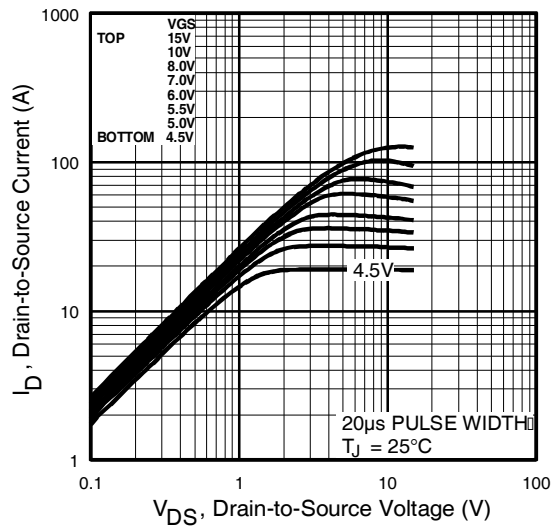
Qualification Information[†]

Qualification Level		Automotive (per AEC-Q101) ^{††}	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		SO-8	MSL1
ESD	Machine Model	N Ch: Class M2(+/- 150V) ^{†††} (per AEC-Q101-002)	P Ch: Class M2(+/- 150V) ^{†††}
	Human Body Model	N Ch : Class H1A(+/- 500V) ^{†††} (per AEC-Q101-001)	P Ch: Class H0(+/- 250V) ^{†††}
	Charged Device Model	N Ch: Class C5(+/- 2000V) ^{†††} (per AEC-Q101-005)	P Ch: Class C5(+/- 2000V) ^{†††}
RoHS Compliant		Yes	

† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/>

†† Exceptions (if any) to AEC-Q101 requirements are noted in the qualification report.

††† Highest passing voltage



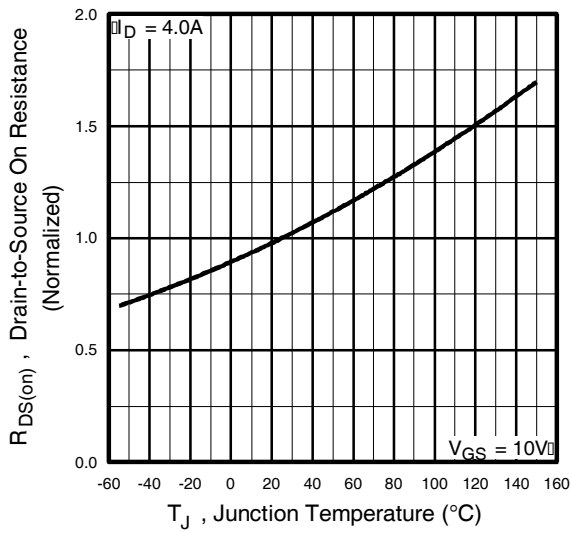


Fig 5. Normalized On-Resistance Vs. Temperature

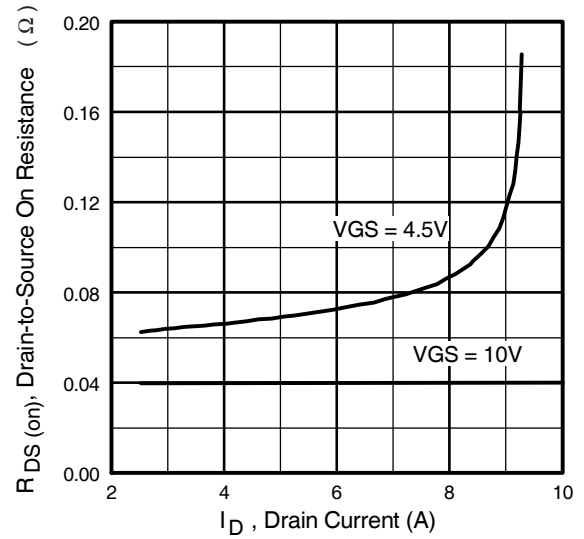


Fig 6. Typical On-Resistance Vs. Drain Current

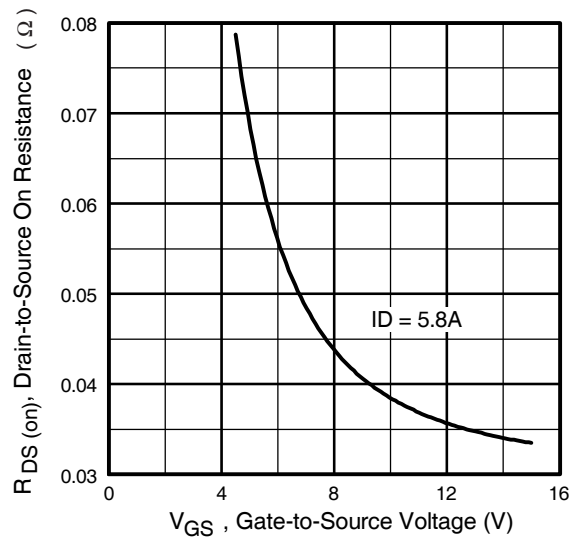


Fig 7. Typical On-Resistance Vs. Gate Voltage

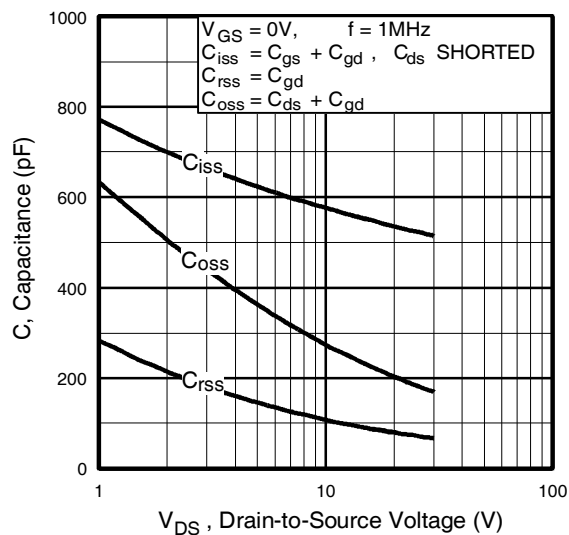


Fig 8. Typical Capacitance Vs. Drain-to-Source Voltage

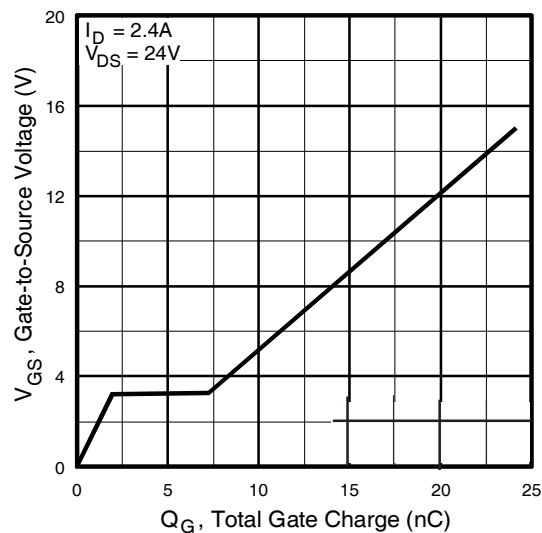


Fig 9. Typical Gate Charge Vs. Gate-to-Source Voltage

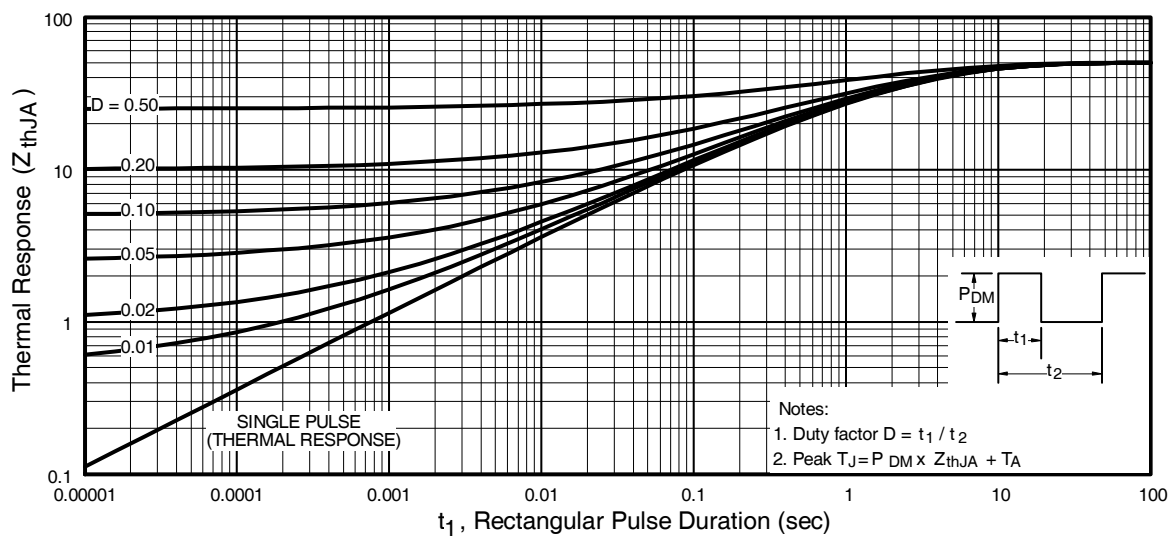


Fig 10. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

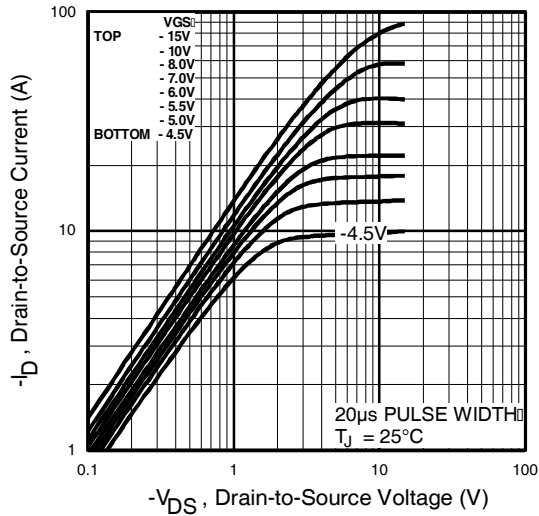


Fig 11. Typical Output Characteristics

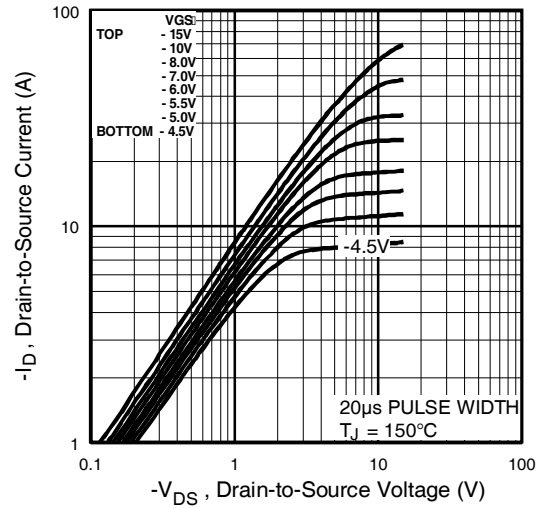


Fig 12. Typical Output Characteristics

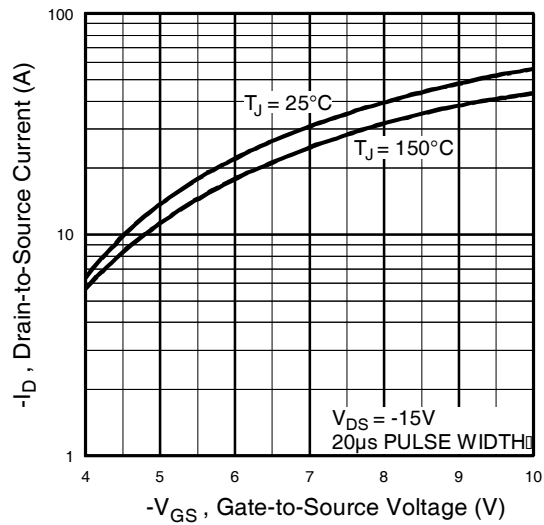


Fig 13. Typical Transfer Characteristics

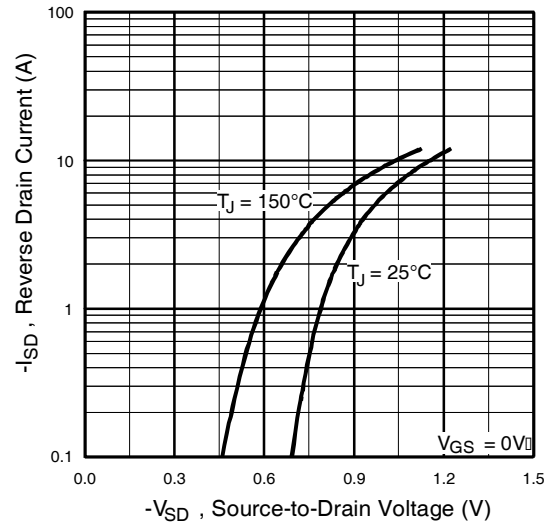


Fig 14. Typical Source-Drain Diode Forward Voltage

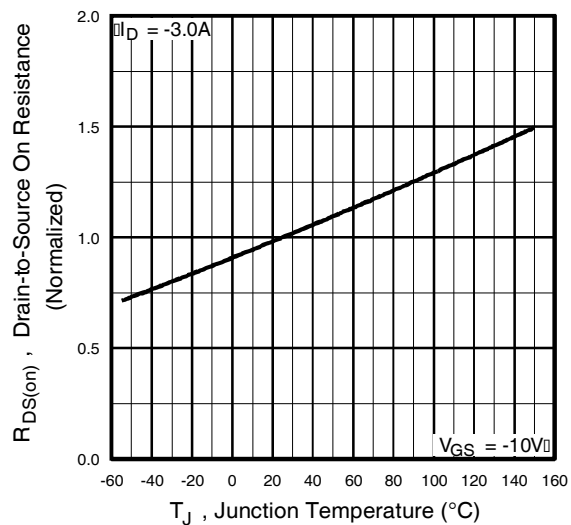


Fig 15. Normalized On-Resistance Vs. Temperature

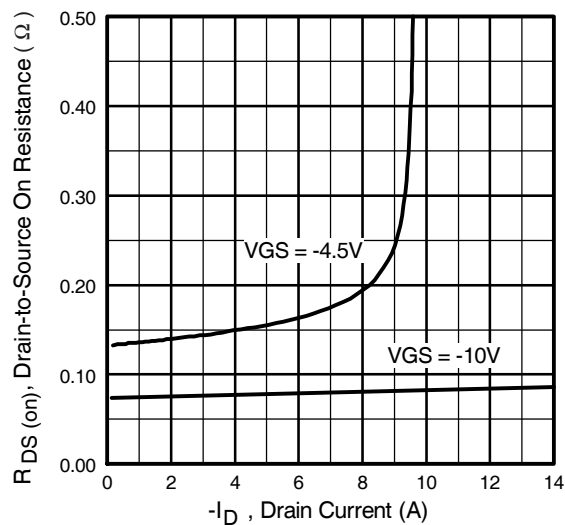


Fig 16. Typical On-Resistance Vs. Drain Current

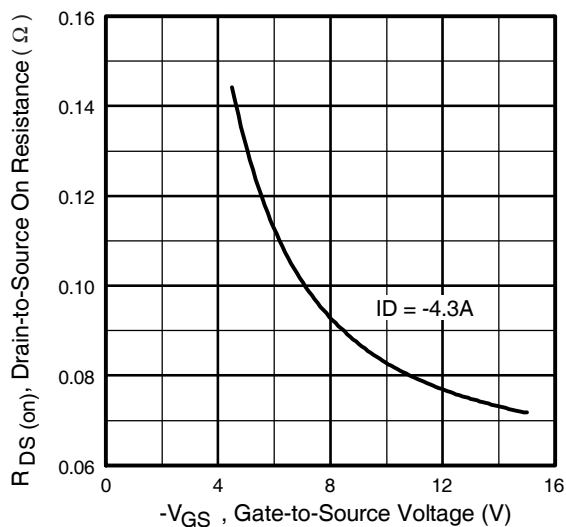


Fig 17. Typical On-Resistance Vs. Gate Voltage

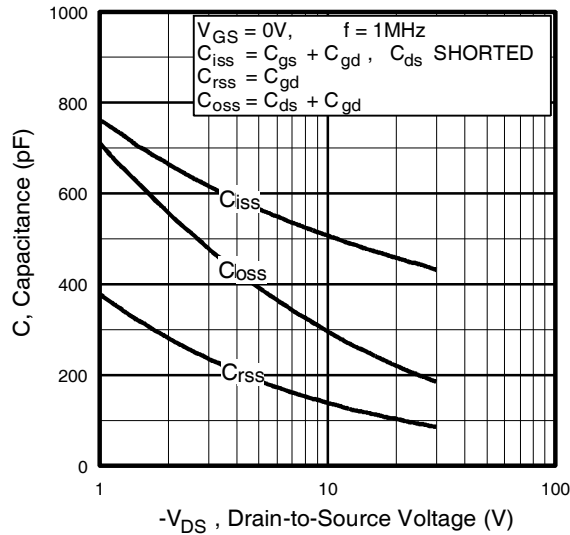


Fig 18. Typical Capacitance Vs. Drain-to-Source Voltage

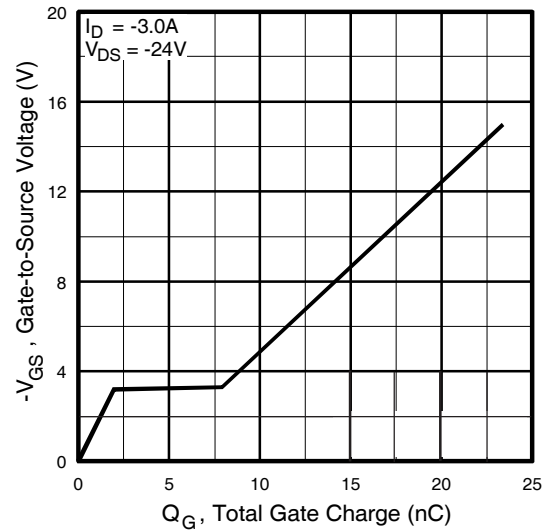


Fig 19. Typical Gate Charge Vs. Gate-to-Source Voltage

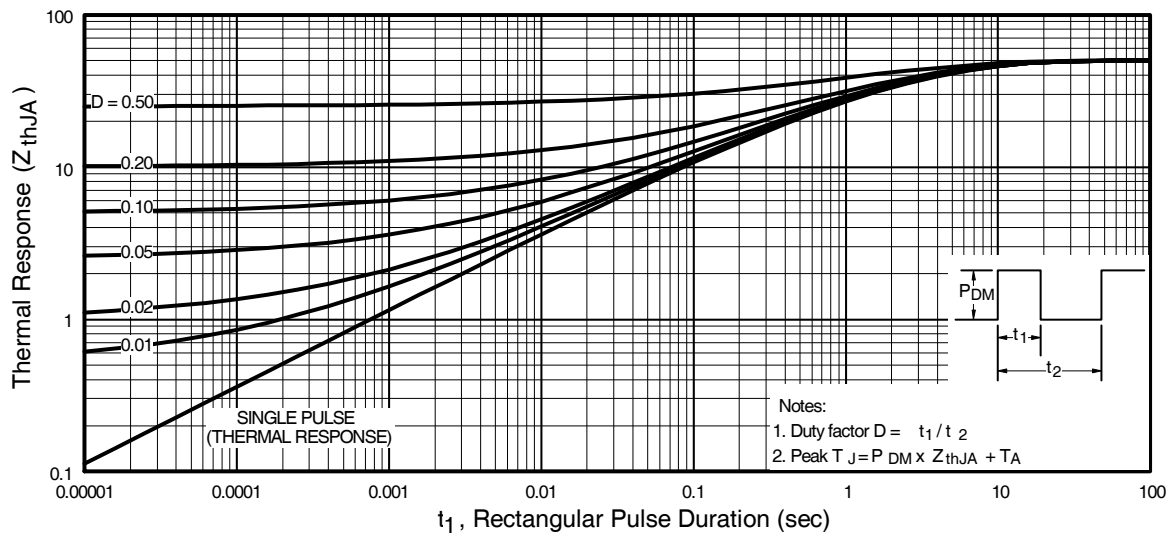
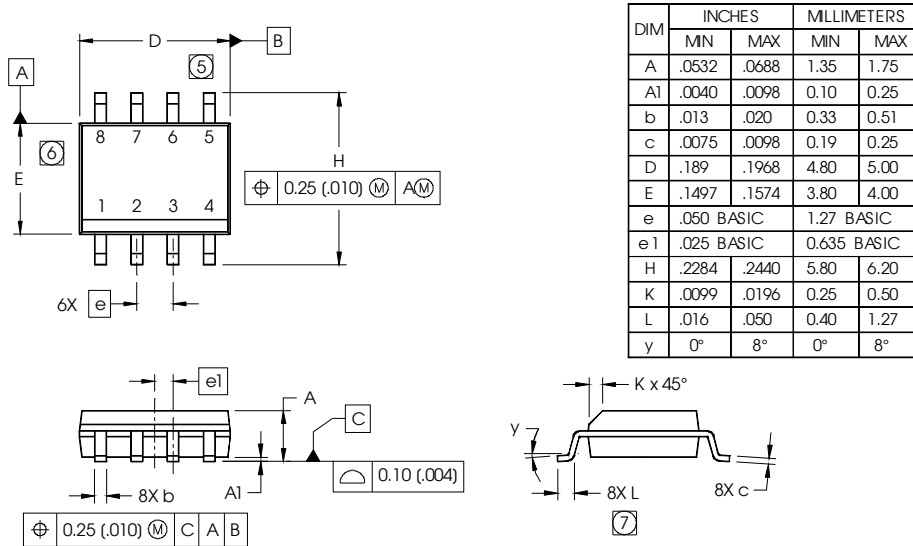


Fig 20. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

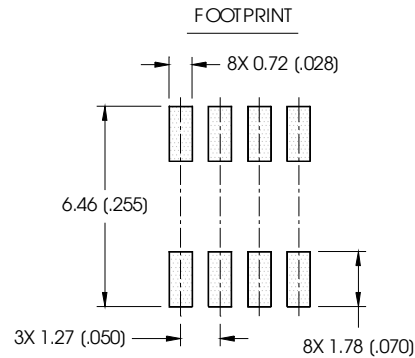
SO-8 Package Outline

Dimensions are shown in millimeters (inches)

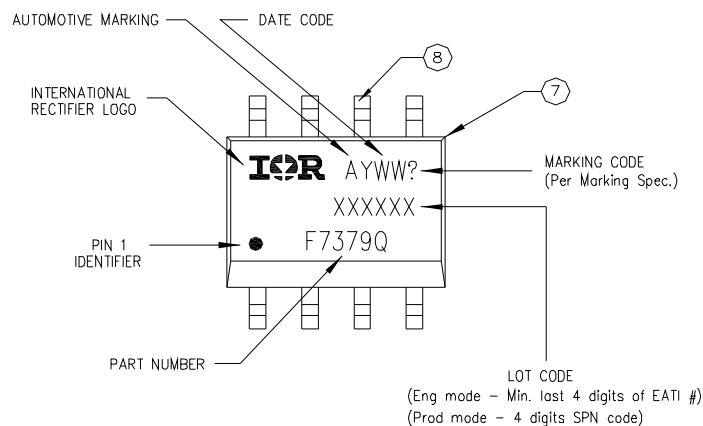


NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.



SO-8 Part Marking

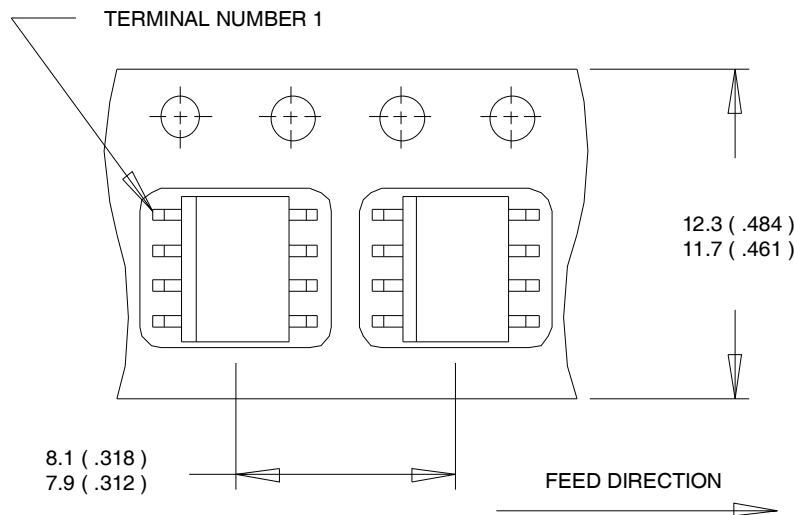


TOP MARKING (LASER)

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

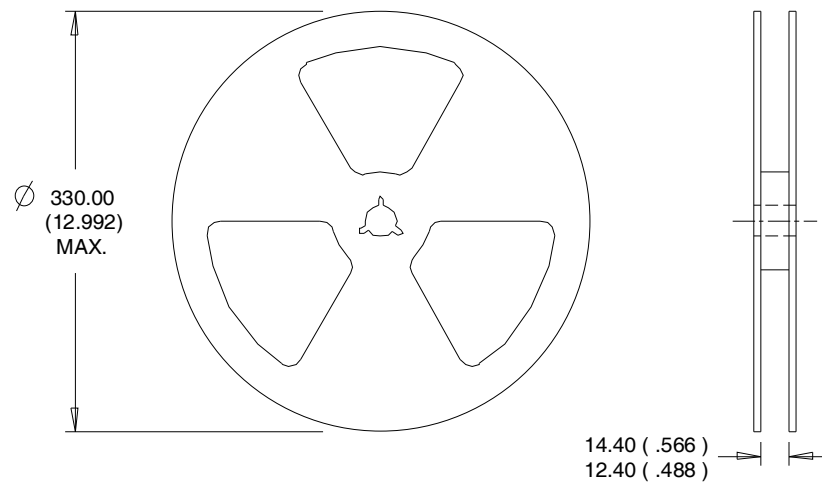
SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



NOTES:

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 10)
- ② N-Channel $I_{SD} \leq 2.4A$, $di/dt \leq 73A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^\circ C$
P-Channel $I_{SD} \leq -1.8A$, $di/dt \leq 90A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^\circ C$
- ③ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.
- ④ Surface mounted on FR-4 board, $t \leq 10sec$.

Ordering Information

Base part	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRF7379Q	SO-8	Tube	95	AUIRF7379Q
		Tape and Reel	4000	AUIRF7379QTR

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For technical support, please contact IR's Technical Assistance Center
<http://www.irf.com/technical-info/>

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